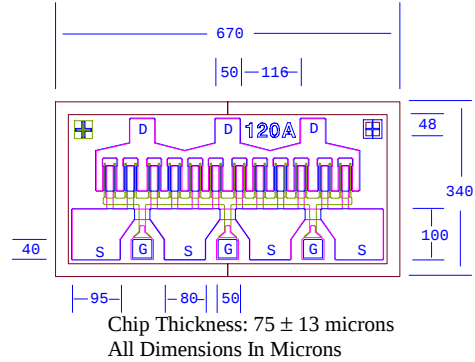


DATA SHEET
High Efficiency Heterojunction Power FET

- +29.5dBm TYPICAL OUTPUT POWER
- 9.5dB TYPICAL POWER GAIN AT 18GHz
- 0.3 X 1200 MICRON RECESSED “MUSHROOM” GATE
- Si₃N₄ PASSIVATION
- ADVANCED EPITAXIAL HETEROJUNCTION PROFILE PROVIDES EXTRA HIGH POWER EFFICIENCY, AND HIGH RELIABILITY
- Idss SORTED IN 30mA PER BIN RANGE


ELECTRICAL CHARACTERISTICS (T_a = 25 °C)

SYMBOLS	PARAMETERS/TEST CONDITIONS	MIN	TYP	MAX	UNIT
P_{1dB}	Output Power at 1dB Compression V _{ds} =8V, I _{ds} =50% I _{dss} f=12GHz f=18GHz	28.0	29.5 29.5		dBm
G_{1dB}	Gain at 1dB Compression V _{ds} =8V, I _{ds} =50% I _{dss} f=12GHz f=18GHz	10.0	12.0 9.5		dB
PAE	Power Added Efficiency at 1dB Compression V _{ds} =8V, I _{ds} =50% I _{dss} f=12GHz		45		%
I_{dss}	Saturated Drain Current V _{ds} =3V, V _{gs} =0V	220	360	500	mA
G_m	Transconductance V _{ds} =3V, V _{gs} =0V	240	380		mS
V_p	Pinch-off Voltage V _{ds} =3V, I _{ds} =3.5mA		-1.0	-2.5	V
BV_{gd}	Drain Breakdown Voltage I _{gd} =1.2mA	-12	-15		V
BV_{gs}	Source Breakdown Voltage I _{gs} =1.2mA	-7	-14		V
R_{th}	Thermal Resistance (Au-Sn Eutectic Attach)		37		°C/W

MAXIMUM RATINGS AT 25°C

SYMBOLS	PARAMETERS	ABSOLUTE ¹	CONTINUOUS ²
V_{ds}	Drain-Source Voltage	12V	8V
V_{gs}	Gate-Source Voltage	-8V	-3V
I_{ds}	Drain Current	I _{dss}	385mA
I_{gsf}	Forward Gate Current	60mA	10mA
P_{in}	Input Power	27dBm	@3dB Compression
T_{ch}	Channel Temperature	175°C	150°C
T_{stg}	Storage Temperature	-65/175°C	-65/150°C
P_t	Total Power Dissipation	3.7W	3.1 W

Note: 1. Exceeding any of the above ratings may result in permanent damage.

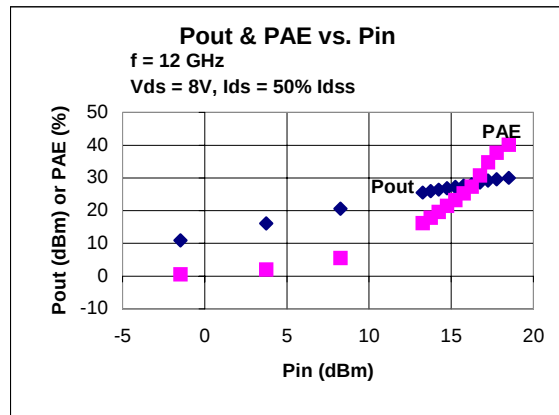
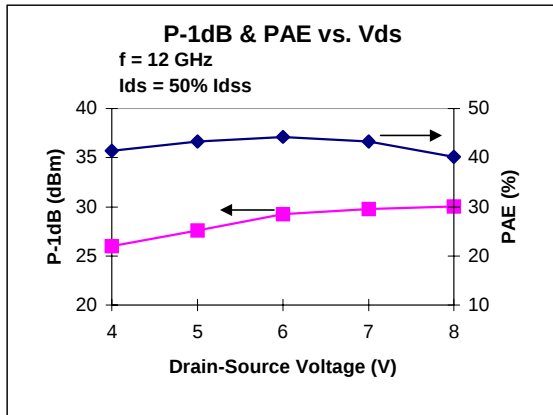
2. Exceeding any of the above ratings may reduce MTTF below design goals.

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DATA SHEET

High Efficiency Heterojunction Power FET



S-PARAMETERS

8V, 1/2 Idss

FREQ (GHz)	--- S11 ---		--- S21 ---		--- S12 ---		--- S22 ---	
	MAG	ANG	MAG	ANG	MAG	ANG	MAG	ANG
1.0	0.890	-98.0	15.016	124.1	0.029	40.0	0.262	-100.0
2.0	0.878	-132.7	9.107	103.0	0.036	26.8	0.278	-127.9
3.0	0.871	-148.6	6.343	91.3	0.037	20.5	0.290	-138.9
4.0	0.871	-157.2	4.875	82.8	0.037	19.1	0.307	-142.9
5.0	0.865	-163.0	3.927	75.8	0.036	18.9	0.325	-145.1
6.0	0.870	-167.0	3.304	69.5	0.036	20.4	0.345	-146.0
7.0	0.873	-169.9	2.838	64.1	0.036	21.0	0.367	-147.1
8.0	0.878	-173.0	2.483	58.4	0.035	21.0	0.391	-148.0
9.0	0.876	-175.1	2.192	53.7	0.034	21.1	0.407	-149.2
10.0	0.879	-177.1	1.960	49.0	0.032	24.3	0.428	-150.3
11.0	0.885	-178.9	1.774	44.4	0.032	25.5	0.450	-152.0
12.0	0.896	-179.2	1.616	39.8	0.032	27.6	0.469	-154.4
13.0	0.904	-177.4	1.474	34.9	0.032	27.3	0.490	-157.4
14.0	0.905	-175.7	1.343	30.3	0.033	27.3	0.507	-160.9
15.0	0.911	-174.5	1.235	25.5	0.033	28.1	0.526	-165.2
16.0	0.906	-173.3	1.126	20.7	0.034	27.9	0.551	-169.8
17.0	0.913	-172.6	1.044	16.4	0.035	25.9	0.576	-174.1
18.0	0.922	-171.3	0.971	11.5	0.036	23.3	0.604	-178.8
19.0	0.925	-169.9	0.899	6.6	0.037	25.8	0.637	-176.8
20.0	0.920	-168.6	0.827	1.8	0.039	24.4	0.663	-172.6
21.0	0.910	-168.0	0.760	-2.2	0.042	25.1	0.686	-169.6
22.0	0.907	-166.8	0.715	-5.9	0.045	26.2	0.711	-167.1
23.0	0.910	-165.7	0.676	-9.1	0.049	27.8	0.736	-165.3
24.0	0.911	-164.1	0.642	-12.8	0.056	28.2	0.758	-163.7
25.0	0.893	-161.9	0.600	-15.8	0.060	31.5	0.766	-162.5
26.0	0.883	-161.5	0.573	-17.2	0.065	31.4	0.763	-163.6

Note: The data included 0.7 mils diameter Au bonding wires:
3 gate wires, 15 mils each; 3 drain wires, 20 mils each; 8 source wires, 7 mils each.